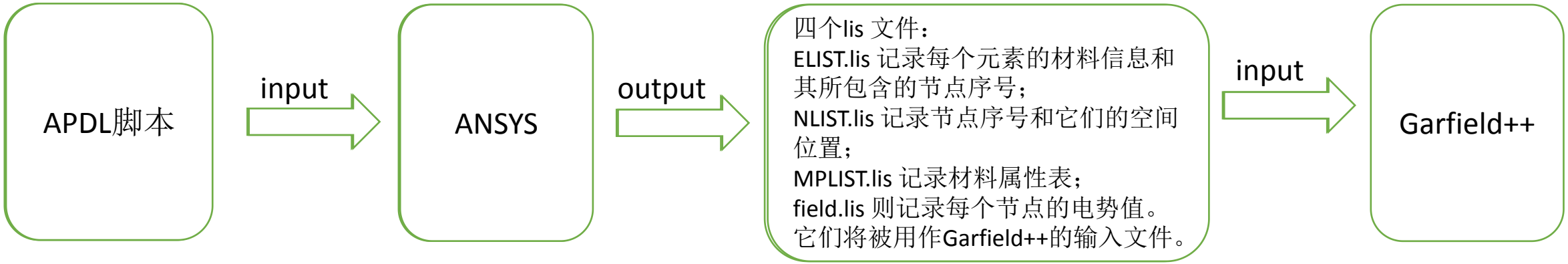
工作报告

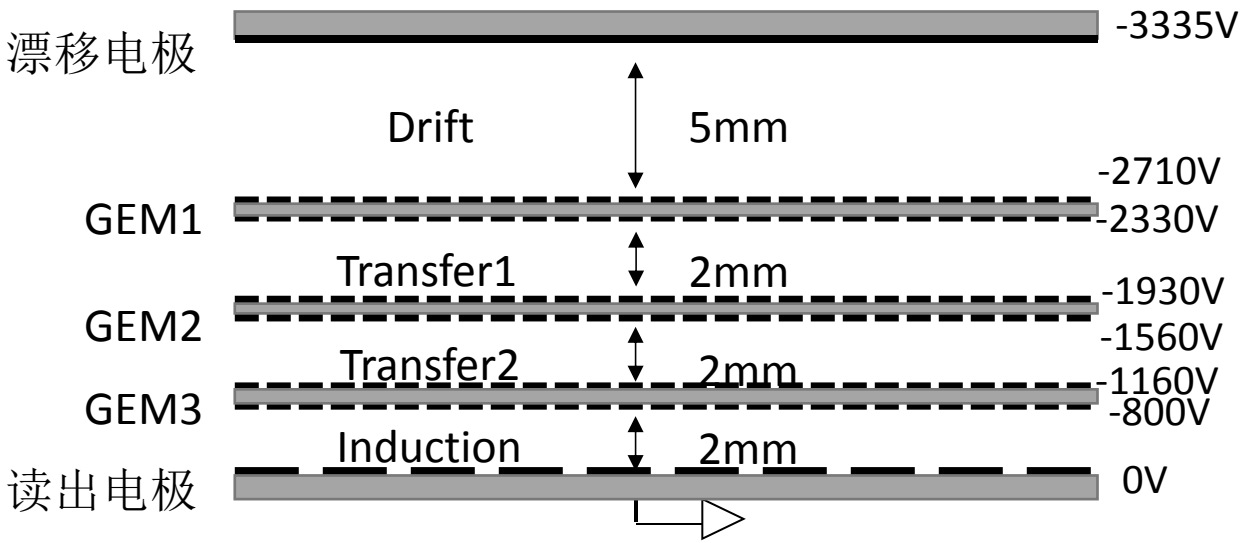
苗楠楠

CGEM 模拟



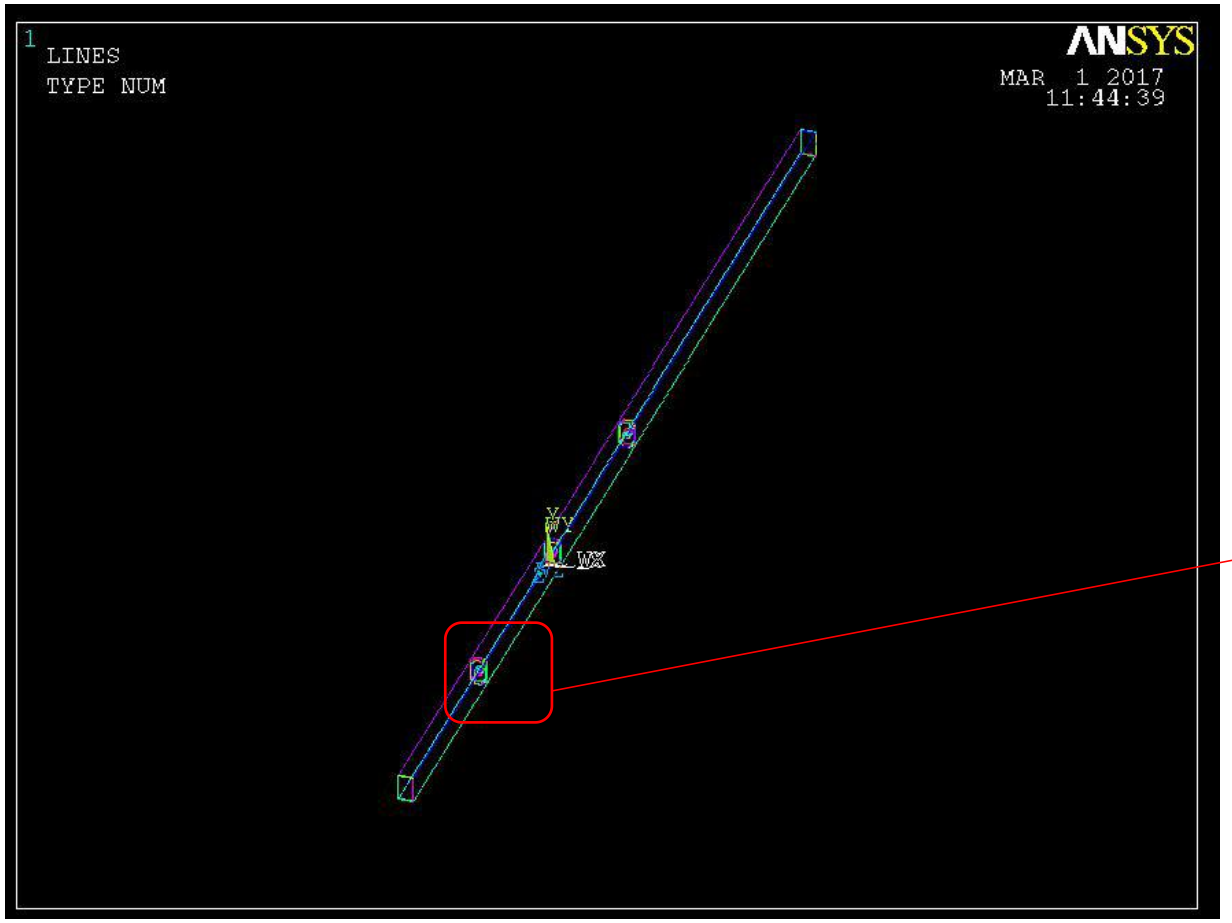
APDL（ANSYS参数化设计语言）脚本：　构建CGEM几何，设置工作电压

*电压设置



	Thickness (mm)	Voltage (V)	Field (kV/cm)
Cathode			
Drift	5	625	1.25 (1.25)
G1_TOP (Cu)	0.003		
Gap	0.050	380	76
G1_BOTTOM (Cu)	0.003		
Transfer1	2	400	2 (3)
G2_TOP(Cu)	0.003		
Gap	0.050	370	74
G2_BOTTOM (Cu)	0.003		
Transfer2	2	400	2 (3)
G3_TOP(Cu)	0.003		
Gap	0.050	360	72
G3_BOTTOM (Cu)	0.003		
Induction	2	800	4 (5)
Anode	ground		

*几何模拟结果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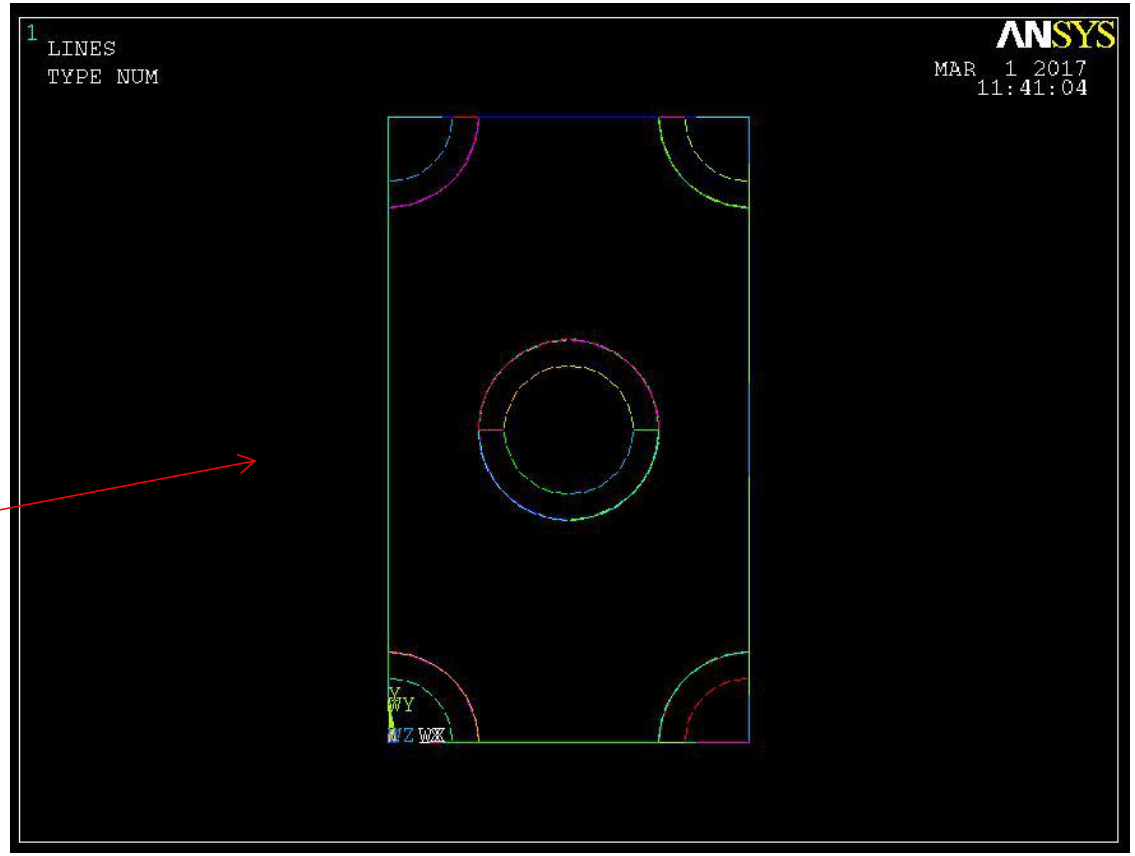
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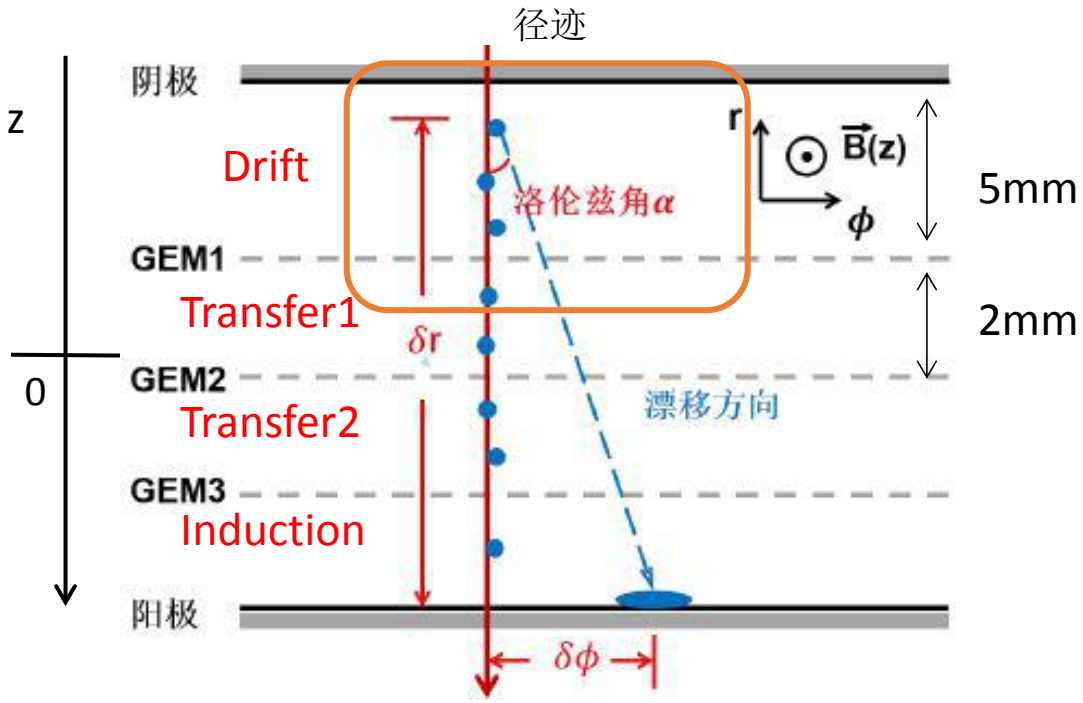
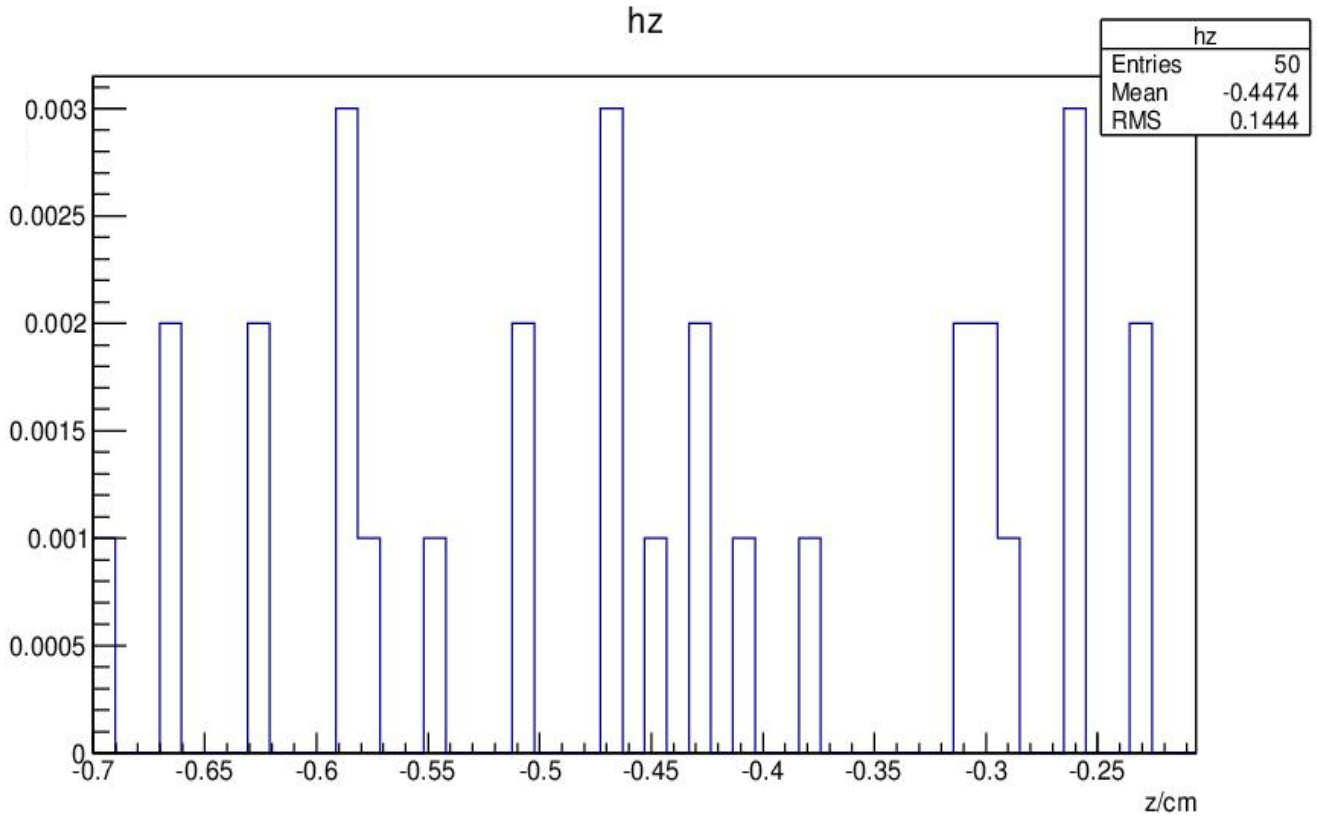
*电子入孔效率统计

漂移区（z向）均分50个bin，取bin中心处每个bin模拟1000次电子（固定x, y 坐标），统计进入GEM1的电子数被上层铜膜吸收所占的比例。





*下一步

- 估算洛伦兹角